

L Number	Hits	Search Text	DB	Time stamp
1	1	("6088127").PN.	USPAT	2002/09/02 10:17
2	1	((("6088127").PN.) and (ground or trap or interconnect or metal or first or second or third or substrate or semiconductor or MOS or transistor or EPI or epitaxial or oxide or burried or insulating or oxidation))	USPAT	2002/09/02 10:21
3	1	("6008127").PN.	USPAT	2002/09/02 10:42
4	1	((("6008127").PN.) and (ground or trap or interconnect or metal or first or second or third or substrate or semiconductor or MOS or transistor or EPI or epitaxial or oxide or burried or insulating or oxidation))	USPAT	2002/09/02 10:21
5	1	((("6008127").PN.) and (ground or trap or low or resistance))	USPAT	2002/09/02 10:51
6	173	257/491	USPAT	2002/09/02 10:52
7	126	257/624	USPAT	2002/09/02 10:52
8	103	257/625	USPAT	2002/09/02 10:52
9	485	257/635	USPAT	2002/09/02 10:52
10	293	257/637	USPAT	2002/09/02 10:52
11	268	257/642	USPAT	2002/09/02 10:52
12	607	257/720	USPAT	2002/09/02 10:52
13	1874	257/774	USPAT	2002/09/02 10:52
-	39	(ground adj trap)	USPAT	2002/08/31 20:26
-	0	(burier adj power adj buss)	USPAT	2002/08/31 20:03
-	1	((ground adj trap)) and (slot and metal and interconnect)	USPAT	2002/08/31 20:06
-	1	((ground adj trap)) and (opening and metal and interconnect)	USPAT	2002/08/31 20:07
-	0	((ground adj trap)) and (first adj metal) and (second adj metal) and (third adj metal)	USPAT	2002/08/31 20:08
-	0	MOS and transistor and ground and (buried adj power) and (first adj metal) and (second adj metal) and (third adj metal)	USPAT	2002/08/31 20:09
-	111	MOS and transistor and ground and (first adj metal) and (second adj metal) and (third adj metal)	USPAT	2002/08/31 20:18
-	0	(MOS and transistor and ground and (first adj metal) and (second adj metal) and (third adj metal)) and (ground adj trap)	USPAT	2002/08/31 20:10
-	1	(MOS and transistor and ground and (first adj metal) and (second adj metal) and (third adj metal)) and (trap and buried and power)	USPAT	2002/08/31 20:17
-	0	(MOS and transistor and ground and (first adj metal) and (second adj metal) and (third adj metal)) and (trap and buried and power and oxidation)	USPAT	2002/08/31 20:18
-	18	MOS and transistor and ground and (first adj metal) and (second adj metal) and (third adj metal) and oxidation	USPAT	2002/08/31 20:18
-	1	("4132856").PN.	USPAT	2002/08/31 20:27

9/2/02